

### **DSA20C100PN**

preliminary

# **Schottky Diode**

 $V_{RRM} = 100 V$ 

 $I_{FAV} = 2x \quad 10 A$ 

 $V_F = 0.71 V$ 

High Performance Schottky Diode Low Loss and Soft Recovery Common Cathode

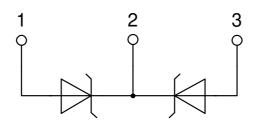
Part number

#### DSA20C100PN



Backside: isolated





#### Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

#### **Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

#### Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

#### **Disclaimer Notice**

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at <a href="https://www.littelfuse.com/disclaimer-electronics">www.littelfuse.com/disclaimer-electronics</a>.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

20200127b





preliminary

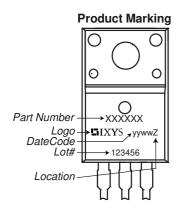
Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			100	٧
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			100	٧
I <sub>R</sub>	reverse current, drain current	$V_R = 100 \text{ V}$	$T_{VJ} = 25^{\circ}C$			200	μΑ
		$V_R = 100 V$	$T_{VJ} = 125$ °C			2	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 10 A	$T_{VJ} = 25^{\circ}C$			0.89	V
		$I_F = 20 A$				1.04	٧
		I <sub>F</sub> = 10 A	T <sub>vJ</sub> = 125°C			0.71	٧
		$I_F = 20 A$				0.87	٧
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 140°C	T <sub>vJ</sub> = 175°C			10	Α
		rectangular $d = 0.5$					i 
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 175°C			0.45	٧
$\mathbf{r}_{F}$	slope resistance } for power lo	oss calculation only				16.1	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	e				4.5	K/W
R <sub>thCH</sub>	thermal resistance case to heatsing	nk			0.5		K/W
P <sub>tot</sub>	total power dissipation		$T_C = 25^{\circ}C$			35	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			240	Α
C¹	junction capacitance	$V_R = 12 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		96		pF



## **DSA20C100PN**

preliminary

Package TO-220FP			Ratings		5			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal					35	Α
T <sub>VJ</sub>	virtual junction temperature				-55		175	°C
Top	operation temperature				-55		150	°C
T <sub>stg</sub>	storage temperature				-55		150	°C
Weight						2		g
M <sub>D</sub>	mounting torque				0.4		0.6	Nm
F <sub>c</sub>	mounting force with clip				20		60	Ν
d <sub>Spp/App</sub>	oroonago distanco on surface	o Letriking dietanoo through air	terminal to terminal	1.6	1.0			mm
$d_{\text{Spb/Apb}}$	creepage distance on surface   striking distance through a		terminal to backside	2.5	2.5			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second	50/60 Hz, RMS; IISOL ≤ 1 mA		2500			V
		t = 1 minute			2100			٧



#### Part description

D = Diode S = Schottky Diode

A = low VF

20 = Current Rating [A]

C = Common Cathode

100 = Reverse Voltage [V] PN = TO-220ABFP (3)

Orde	ing	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Stanc	ard	DSA20C100PN	DSA20C100PN	Tube	50	503516

Similar Part	Package	Voltage class
DSA20C100PB	TO-220AB (3)	100

<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$	)—[R_o_]-	Schottky		
V <sub>0 max</sub>	threshold voltage	0.45		V
$R_{0 max}$	slope resistance *	12.9		$m\Omega$

IXYS reserves the right to change limits, conditions and dimensions.

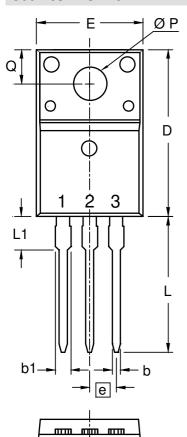
Data according to IEC 60747and per semiconductor unless otherwise specified

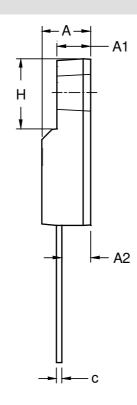
20200127b



preliminary

### Outlines TO-220FP





Dim.	Millim	neters	Inches		
DIIII.	min	max	min	max	
Α	4.50	4.90	0.177	0.193	
A1	2.34	2.74	0.092	0.108	
A2	2.56	2.96	0.101	0.117	
b	0.70	0.90	0.028	0.035	
С	0.45	0.60	0.018	0.024	
D	15.67	16.07	0.617	0.633	
Е	9.96	10.36	0.392	0.408	
е	2.54	BSC	0.100	100 BSC	
Н	6.48	6.88	0.255	0.271	
L	12.68	13.28	0.499	0.523	
L1	3.03	3.43	0.119	0.135	
ØΡ	3.08	3.28	0.121	0.129	
Q	3.20	3.40	0.126	0.134	

